

BGA619

Silicon Germanium

High IP3 PCS Low Noise Amplifier

Wireless
Silicon Discretes



Never stop thinking.

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BGA619**Data Sheet****Revision History: April 2004**

Previous Version: February 2004

Page	Subjects (major changes since last revision)
4	Marking corrected

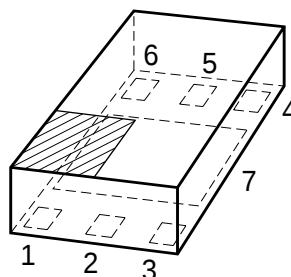
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Silicon Germanium High IP3 PCS Low Noise Amplifier

BGA619

Features

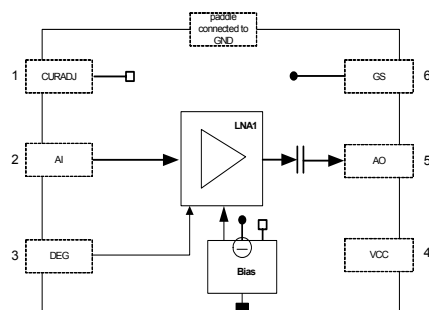
- B7HF silicon germanium technology
- Tiny P-TSLP-7-1 leadless package
- RF output-port internally pre-matched to 50Ω
- Low external component count
- Three gain steps
- Power off function
- High IP3 in all modes
- Typical supply voltage: 2.78 V



Applications

- 1.9 GHz PCS wireless frontends (CDMA2000)

P-TSLP-7-1



Description

The BGA619 is a high IP3 PCS low noise amplifier, designed for 1.9GHz applications.

Internal biasing provides stable current conditions for all gain modes over temperature range.

Using the pin GS the BGA619 can be switched between three gain modes (HIGH, MID & LOW) and the OFF mode.

ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Package	Marking	Chip
BGA619	P-TSLP-7-1	BT	T1544

Pin Definition and Function

Pin No.	Symbol	Function
1	CURADJ	Current adjust LNA
2	AI	LNA input
3	DEG	RF ground
4	VCC	Supply voltage LNA
5	AO	LNA output
6	GS	Gain step control
7	GND	Ground

Maximum Rating

Parameter	Symbol	Limit value	Unit
Voltage at pin VCC	VCC	-0.3 ... 3.6	V
Voltage at pin AI (LNA input)	AI	-0.3 (min.)	V
Voltage at pin AO (LNA output)	AO	-0.3 ... $V_{VCC}+0.3$ 3.6 (max.)	V
External resistor	R_{CURADJ}	6 (min.)	k Ω
Current into VCC	ICC	11	mA
Junction temperature	T_j	150	°C
Ambient temperature range	T_A	-35... 85	°C
Storage temperature range	T_{STG}	-40 ... 150	°C
ESD capability (HBM: JESD22A-114)			
RF pin AI	V_{ESD}	<500	V
all other pins		1000	

Notes:

All Voltages refer to GND-Node

Electrical Characteristics

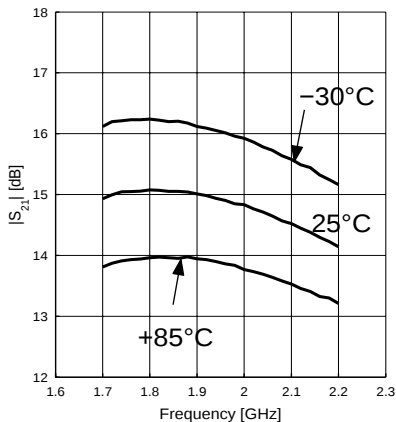
$T_A=25^{\circ}\text{C}$: $V_{CC}=2.78\text{V}$, $R_{LNA_Curadj} = 15\text{k}\Omega$, frequency=1.96GHz, HIGH: $GS=2.3\text{V}$, MID: $GS=1.7\text{V}$, LOW: $GS=1.0\text{V}$, unless otherwise noted; measured on BGA619 Appl. Board V1.0 including PCB losses

Parameter	Symbol	GS mode	min.	typ.	max.	Unit
Supply current	I_{cc}	HIGH		6.5		mA
		MID		4.5		
		LOW		2.9		
		OFF		280		
	μA					
Power gain	S_{21}	HIGH		14.9		dB
		MID		2.2		
		LOW		-9.5		
Noise figure ($Z_s = 50\Omega$)	NF	HIGH		1.5		dB
		MID		8		
		LOW		16		
Input Return Loss	S_{11}	HIGH		10.5		dB
		MID		8.5		
		LOW		12.5		
Output Return Loss	S_{22}	HIGH		11.5		dB
		MID		13		
		LOW		13		
Reverse isolation	S_{12}	HIGH		25		dB
		MID		21		
		LOW		23		
Power gain settling time (within 1dB of the final gain)	t_s	ALL		70		μs
3rd order input intercept point f1= 1950MHz, f2= f1 +/-1MHz P(f1,f2)= -30dBm P(f1,f2)= -27dBm P(f1,f2)= -15dBm	IIP_3					dBm
		HIGH		7		
		MID		6.5		
		LOW		15		
Gain step input voltage	GS	HIGH	2.2		2.4	V
		MID	1.6		1.8	
		LOW	0.9		1.1	
		OFF	0.0		0.3	
Gain control current	I_{GS}	HIGH			95	μA
		OFF			-55	

Typical measurement results HIGH Gain Mode; $T_A = 25^\circ\text{C}$

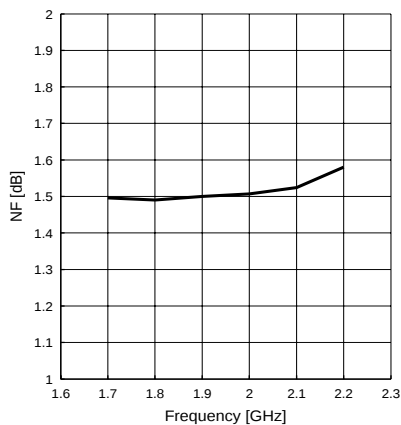
Gain $|S_{21}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 6.5\text{mA}$



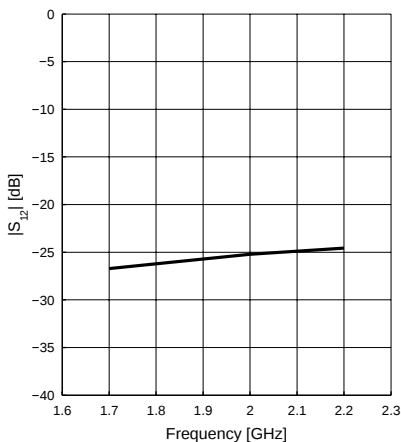
Noise Figure $NF = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 6.5\text{mA}$, Gain = 14.9dB



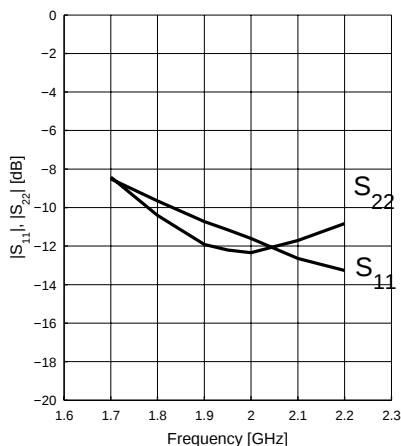
Reverse Isolation $|S_{12}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 6.5\text{mA}$



Matching $|S_{11}|, |S_{22}| = f(f)$

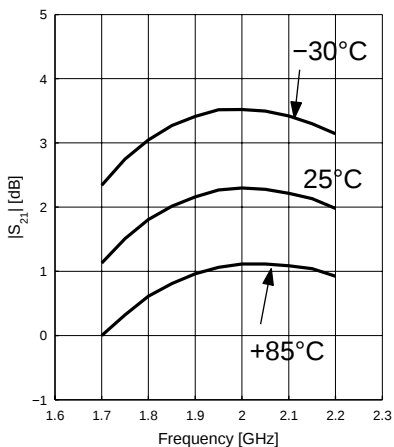
$V_{CC} = 2.78\text{V}$, $I_{CC} = 6.5\text{mA}$



Typical measurement results MID Gain Mode; $T_A = 25^\circ\text{C}$

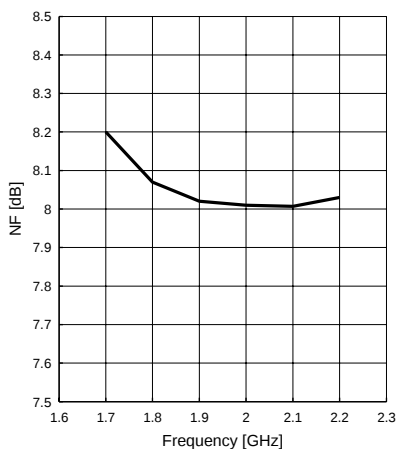
Gain $|S_{21}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 4.5\text{mA}$



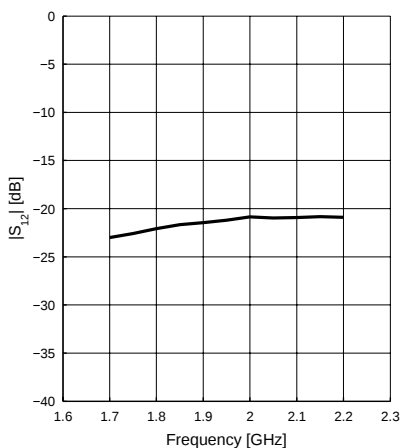
Noise Figure $NF = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 4.5\text{mA}$, Gain = 2.2dB



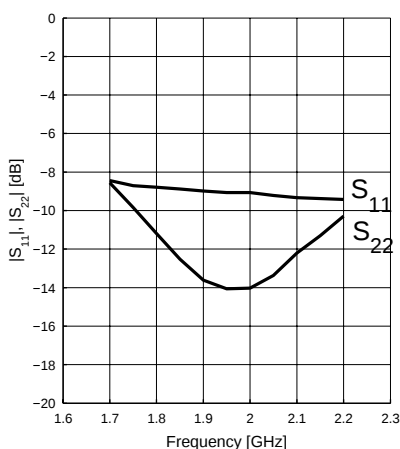
Reverse Isolation $|S_{12}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 4.5\text{mA}$



Matching $|S_{11}|, |S_{22}| = f(f)$

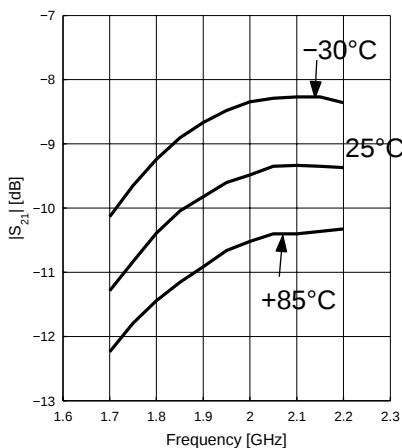
$V_{CC} = 2.78\text{V}$, $I_{CC} = 4.5\text{mA}$



Typical measurement results LOW Gain Mode; $T_A = 25^\circ\text{C}$

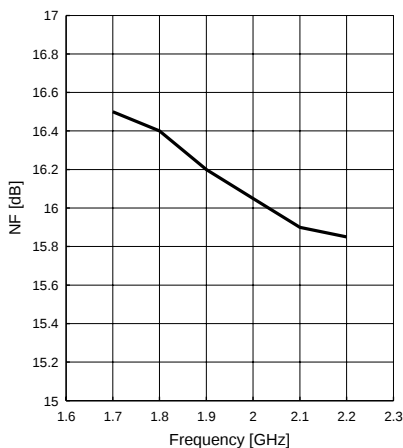
Gain $|S_{21}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 2.9\text{mA}$



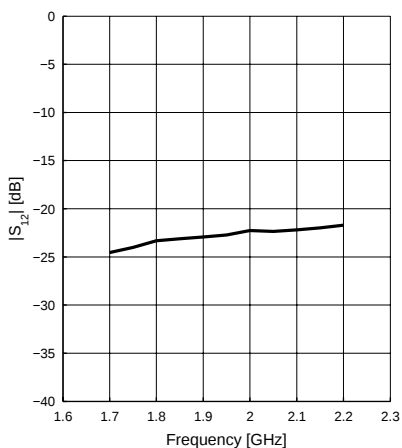
Noise Figure $NF = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 2.9\text{mA}$, Gain = -9.5dB



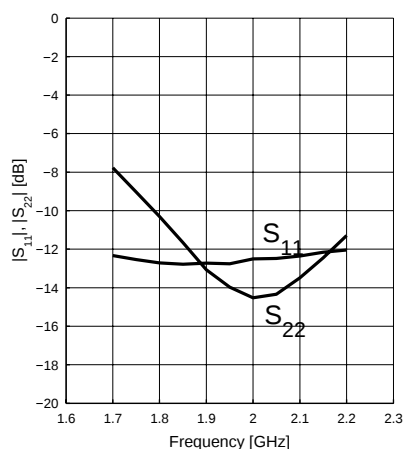
Reverse Isolation $|S_{12}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 2.9\text{mA}$



Matching $|S_{11}|, |S_{22}| = f(f)$

$V_{CC} = 2.78\text{V}$, $I_{CC} = 2.9\text{mA}$

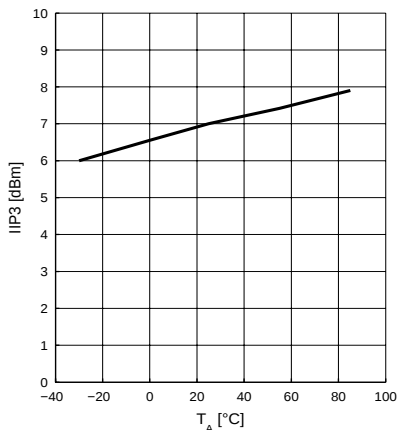


Typical measurement results 3rd Order Intercept Point

High Gain Mode

Intercept Point 3rd O. $IIP3 = f(T_A)$

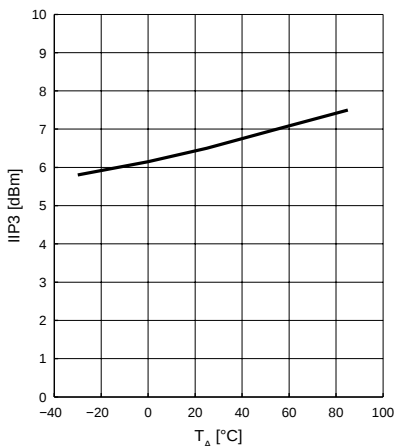
$V_{CC} = 2.78V$, $I_{CC} = 6.5mA$, Gain = 14.9dB



Mid Gain Mode

Intercept Point 3rd O. $IIP3 = f(T_A)$

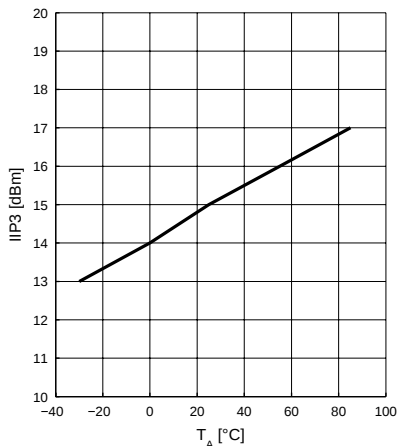
$V_{CC} = 2.78V$, $I_{CC} = 4.5mA$, Gain = 2.2dB



Low Gain Mode

Intercept Point 3rd O. $IIP3 = f(T_A)$

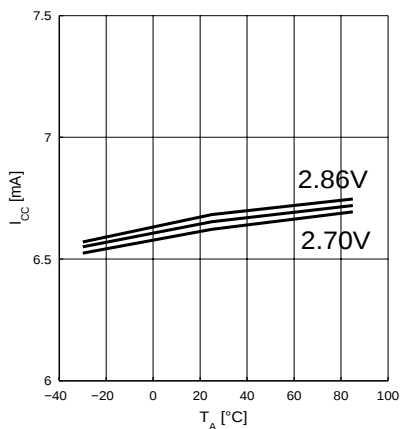
$V_{CC} = 2.78V$, $I_{CC} = 2.9mA$, Gain = -9.5dB



Typical measurement results Supply Current vs.Temp & Supply (2.7..2.86V)

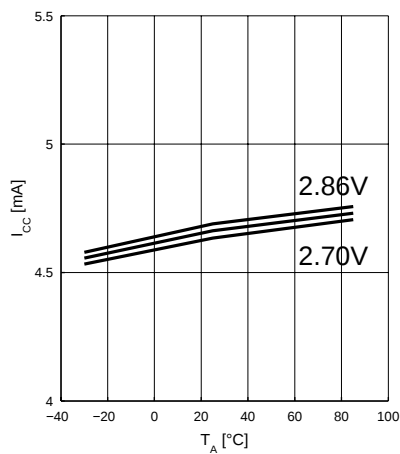
HIGH Gain Mode

Supply current vs. Temp. $I_{CC} = f(T_A, V_{CC})$



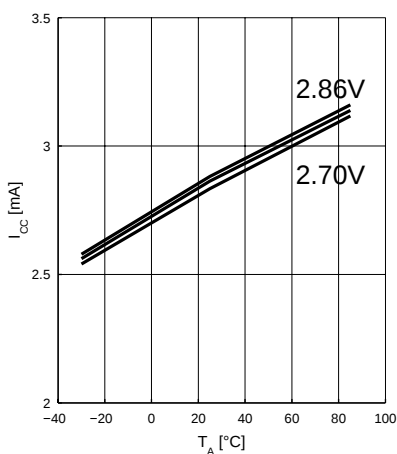
MID Gain Mode

Supply current vs. Temp. $I_{CC} = f(T_A, V_{CC})$



LOW Gain Mode

Supply current vs. Temp. $I_{CC} = f(T_A, V_{CC})$

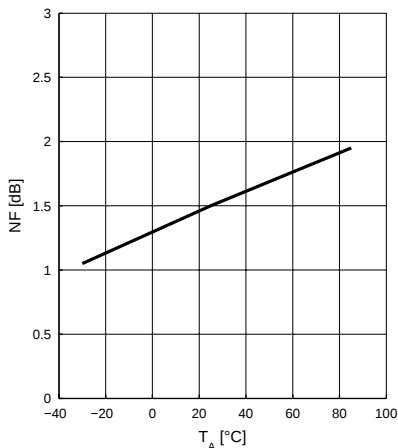


Typical measurement results Noise Figure

HIGH Gain Mode

Noise Figure $NF = f(T_A)$

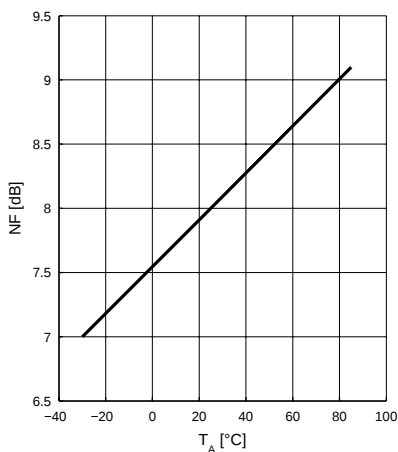
$V_{CC} = 2.78V$, $I_{CC} = 6.5mA$, Gain = 14.9dB



MID Gain Mode

Noise Figure $NF = f(T_A)$

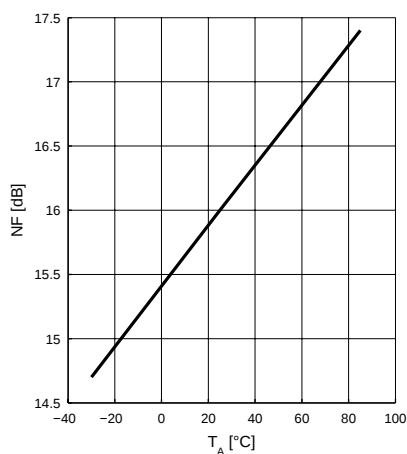
$V_{CC} = 2.78V$, $I_{CC} = 4.5mA$, Gain = 2.2dB



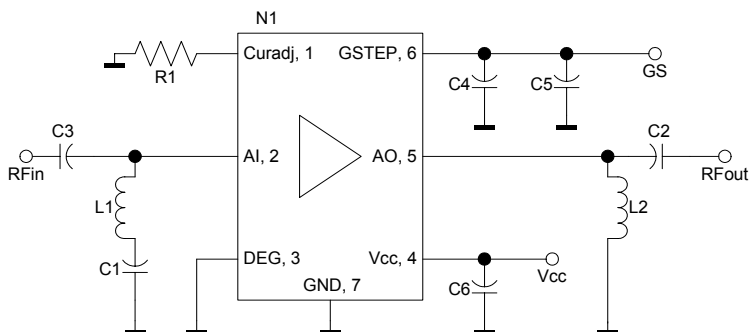
LOW Gain Mode

Noise Figure $NF = f(T_A)$

$V_{CC} = 2.78V$, $I_{CC} = 2.9mA$, Gain = -9.5dB



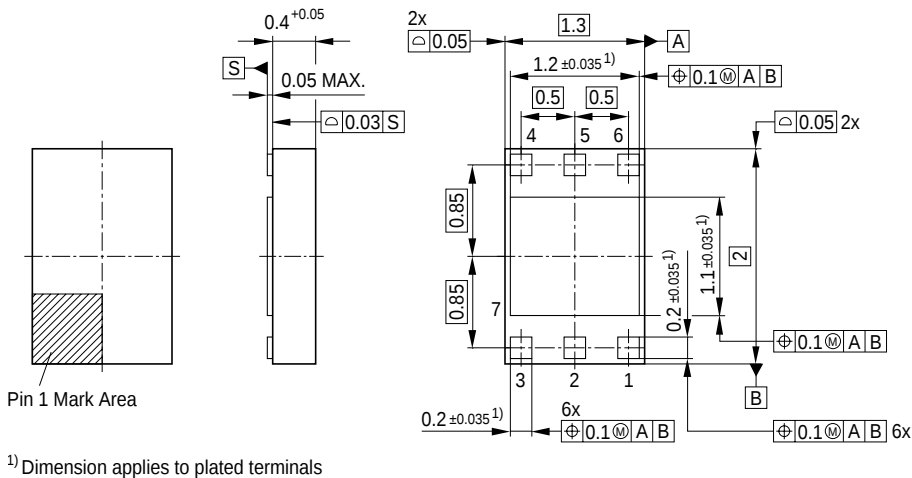
PCB Board Configuration



Bill of Materials

Name	Value	Package	Manufacturer	Function
R1	15 k Ω	0402	various	bias resistance
L1	3.3 nH	0402	various	LF trap & input matching
L2	4.7 nH	0402	various	output matching
C1	10 nF	0402	various	LF trap
C2	10 pF	0402	various	DC block
C3	10 pF	0402	various	DC block
C4	10p	0402	various	control voltage filtering - OPTIONAL
C5	1 nF	0402	various	control voltage filtering - OPTIONAL
C6	1 nF	0402		supply filtering
N1	BGA619	P-TSLP-7-1	Infineon	SiGe LNA

Package Outline



Tape & Reel Outline

